Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	141	stack\$3 fault with defect same metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:46
L2	1	stack\$3 fault with defect with captur\$3 same metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:47
L3	3	stack\$3 fault with defect same captur\$3 same metal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:47
L4	0	stack\$3 fault and intricsic getter\$3 and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:48
L5	48	stack\$3 fault and intrinsic getter\$3 and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:48
L6	3	stack\$3 fault and intrinsic getter\$3 and (support or base) near wafer and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:49
L7	19	stack\$3 fault and intrinsic getter\$3 and (handle or support or base) near wafer and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:50

L8	19	intrinsic getter\$3 same (handle or support or base) near wafer and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 08:56
L9	90	stack\$3 fault with cop	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:20
L10	22	stack\$3 fault with cop and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:21
L11	0	intrinsic getter\$3 same (handle or support or base) near wafer and soi and osf	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:27
L12	12	intrinsic getter\$3 same (handle or support or base) near wafer and soi and stack\$3 with fault	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:27
L13	28	getter\$3 same (handle or support or base) near wafer and soi and stack\$3 with fault	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:28
L14		stack\$3 with fault same getter\$3 same (handle or support or base) near wafer and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/04 09:29

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L15	2	("6008110").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 10:22
L16	2	("5753353").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 10:23
L17	1641	(438/455).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 10:27 ·
L18	1180	(438/458).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/04 10:28
S1		oxidation stack\$3 fault	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:38
S2	3	oxidation stack\$3 fault and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:38
S3	104	oxidation with stack\$3 fault and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:38

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S4	82	oxidation with stack\$3 fault and soi and bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:40
S5	56	oxidation with stack\$3 fault and soi and bond\$3 and implant\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:40
S6	30	oxidation with stack\$3 fault and soi and bond\$3 and implant\$3 with (hydrogen or noble gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/01/30 20:42
S7	0	support wafer with osf	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 18:46
S8	0	support wafer same oxidation stacking faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 18:47
S9	0	support wafer and oxidation stacking faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 18:47
S10	16	support wafer and stacking faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 18:48

			LIC DCCL	453	ON	2000/02/22 40 42
S11	3	support wafer same stacking faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 18:48
S12	471	soi and stacking faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:33
S13	98	soi and stacking faults and implant\$3 with hydrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:34
S14	91	soi and stacking faults and implant\$3 with hydrogen and bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:34
S15	1	soi and stacking faults same support with wafer and implant\$3 with hydrogen and bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:35
S16	0	soi and stacking faults same support with wafer and implant\$3 with hydrogen and bond\$3 cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:36
S17		soi and stacking faults same support with wafer and implant\$3 with hydrogen and bond\$3 and cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:36

S18		soi and stacking faults same wafer and implant\$3 with hydrogen and bond\$3 and cleavage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 19:37
S19	144	endo-akihiko.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 20:14
S20	53	endo-akihiko.in. and soi	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 20:14
S21	6.	endo-akihiko.in. and soi and faults	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/02/03 20:16